

Performance

- Technology: 0.25um Power GaN HEMT
- Frequency: 5.3~5.9GHz
- Typical Pout : 56dBm
- Typical Gain: 11dB
- Typical PAE: 50%
- Bias: 50V/-2.4V@16A
- Package: Metal Ceramic

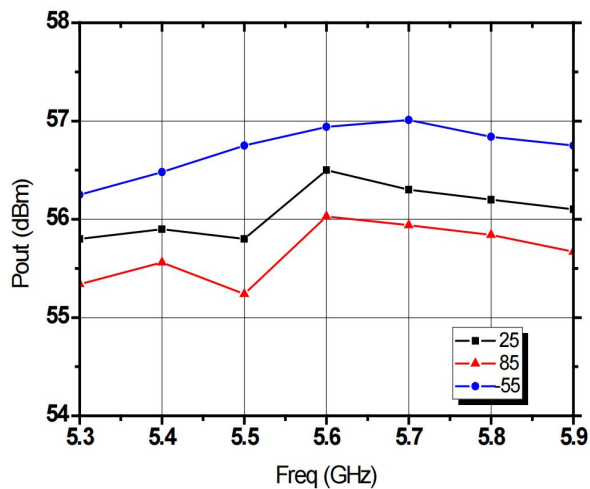


Electrical Specifications (TA=25°C, Vd=50V, Vg= -2.4V, F: 5.3~5.9GHz, PL=1ms, D.C=20%)

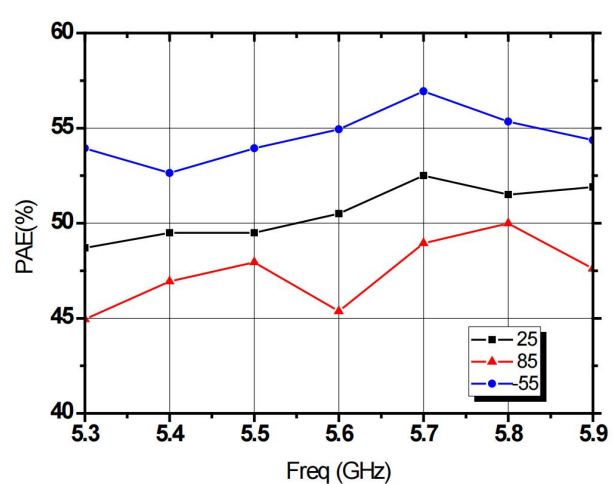
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	56	-	dBm
Gp	Power Gain	-	11	-	dB
η_{add}	Power Added Efficiency	-	50	-	%
ΔGp	Gain Flatness	-0.8	-	+0.8	dB

Test Curves

Pout&Freq. @ Different Temp.



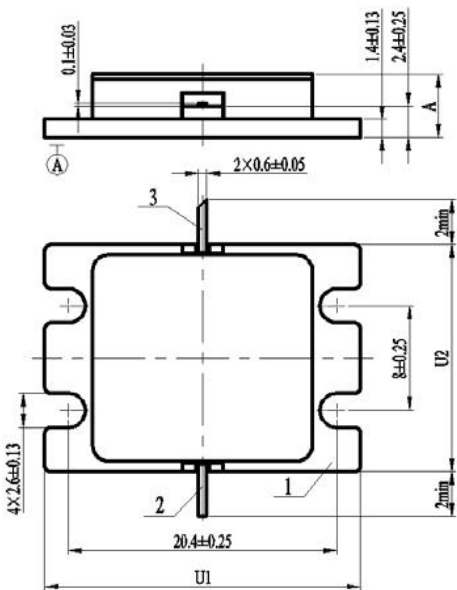
PAE&Freq. @ Different Temp.

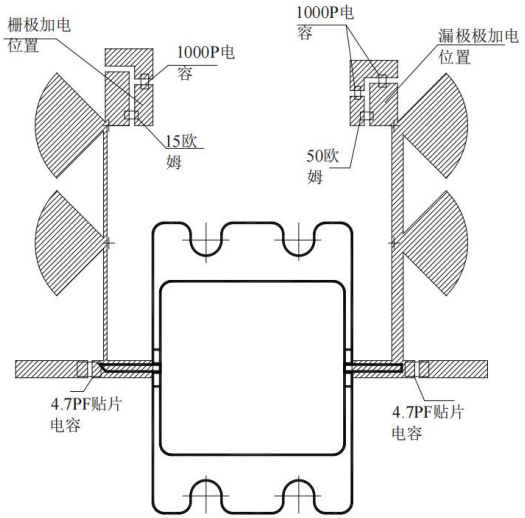


Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	60V	
Vg	Grid Voltage	-5V	
Tch	Channel Temperature	225°C	【1】
Tm	Mounting Temperature	300°C	1 min, N2 Protection
Tstg	Storage Temperature	-55~175°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing	Dimension Symbols														
 The drawing shows a top view and a side view of the transistor. The top view is a square with rounded corners, with dimensions U1 (width) and U2 (height). The side view shows the thickness of the device, with dimensions A (total thickness) and 0.1±0.03 (top layer thickness). Other dimensions include 2×0.6±0.05 (top layer width), 1.4±0.13 (top layer height), 2.4±0.25 (top layer width), 2min (bottom layer height), 8±0.25 (bottom layer height), 4×2.6±0.13 (bottom layer width), 20.4±0.25 (bottom layer width), 2 (bottom layer width), 1 (bottom layer width), 3 (bottom layer width), and 2min (bottom layer height).	<table><tr><th rowspan="2">Symbol</th><th colspan="2">Value (unit: mm)</th></tr><tr><th>Min.</th><th>Max.</th></tr><tr><td>U1</td><td>23.80</td><td>24.20</td></tr><tr><td>U2</td><td>17.20</td><td>17.60</td></tr><tr><td>A</td><td>-</td><td>5.2</td></tr></table>	Symbol	Value (unit: mm)		Min.	Max.	U1	23.80	24.20	U2	17.20	17.60	A	-	5.2
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	Min.	Max.													
U1	23.80	24.20													
U2	17.20	17.60													
A	-	5.2													

Application Circuit
 The diagram shows the transistor with various components and labels. The labels include: 栅极加电位置 (Gate power position), 1000P电容 (1000P capacitor), 15欧姆 (15 ohms), 50欧姆 (50 ohms), 漏极加电位置 (Drain power position), 4.7PF贴片电容 (4.7PF surface mount capacitor), and 500P电容 (500P capacitor).

Note:

- (1) This product is an internal matching tube, with input and output impedance values of 50 ohms;
- (2) The power-on sequence shall be in strict accordance with the sequence of applying negative power first and then positive power. When power-off, the leakage voltage shall be reduced first and then the grid voltage shall be reduced;
- (3) This product is a high-power device. Pay attention to heat dissipation during use. The higher the shell temperature is, the shorter the service life is. The service temperature should not be higher than 80 °C;
- (4) This product is an electrostatic sensitive device. It needs to pay attention to electrostatic protection during storage and use, and it needs to be grounded well during use.